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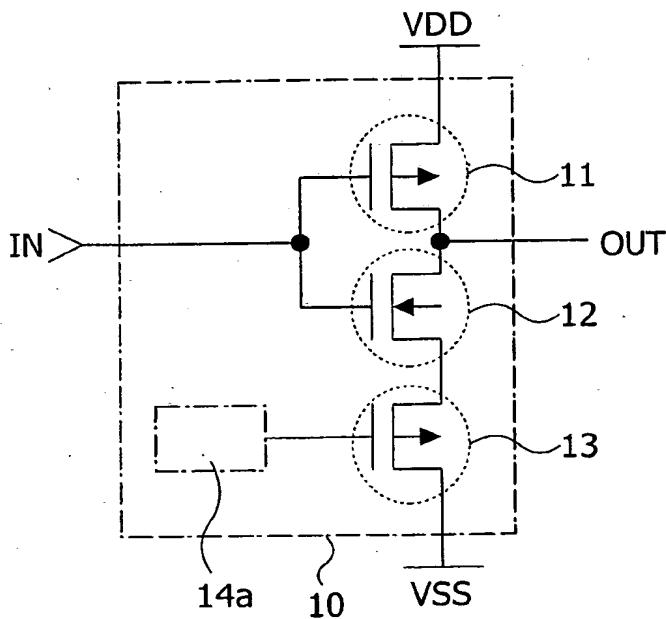
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(54) Title: SEMICONDUCTOR DEVICE AND ELECTRONIC APPLIANCE USING THE SAME



(57) Abstract: A semiconductor device with less power consumption and an electronic appliance using the same. The semiconductor device of the invention is supplied with a first potential from a high potential power source and a second potential from a low potential power source. Upon input of a first signal to an input node, an output node outputs a second signal. With the semiconductor device of the invention, a potential difference of the second signal can be controlled to be smaller than a potential difference between the first potential and the second potential, thereby power consumption required for charging/discharging wires can be reduced.

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